TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

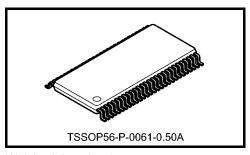
TC74VCXR162543FT

Low-Voltage 16-Bit Registered Transceiver with 3.6-V Tolerant Inputs and Outputs

The TC74VCXR162543FT is a high-performance CMOS 16-bit registered transceiver. Designed for use in 1.8-V, 2.5-Vor 3.3-V systems, it achieves high-speed operation while maintaining the CMOS low power dissipation.

It is also designed with overvoltage tolerant inputs and outputs up to $3.6\ V.$

The TC74VCXR162543FT can be used as two 8-bit transceivers or one 16-bit transceiver. Separate latch-enable ($\overline{\text{LEAB}}$ or ($\overline{\text{LEBA}}$) and output-enable ($\overline{\text{OEAB}}$ or $\overline{\text{OEBA}}$) inputs are provided for each register to permit independent control in either direction of data flow.



Weight: 0.25 g (typ.)

The A-to-B enable (CEAB) input must be low in order to enter

data from A or to output data from B. If CEAB is low and LEAB is low, the A-to-B latches are transparent; a subsequent low-to-high transition of $\overline{\text{LEAB}}$ puts the Alatches in the storage mode. With $\overline{\text{CEAB}}$ and $\overline{\text{OEAB}}$ both low, the 3-state B outputs are active and reflect the data present at the output of the A latches.

Data flow from B to A is similar but requires using the CEBA, LEBA, and OEBA inputs.

When the OE input is high, the outputs are in a high-impedance state. This device is designed to be used with 3-state memory address drivers, etc.

The $26-\Omega$ series resistor helps reducing output overshoot and undershoot without external resistor.

All inputs are equipped with protection circuits against static discharge.

Features (Note)

- 26-Ω series resistors on outputs
- Low-voltage operation: V_{CC} = 1.8 to 3.6 V
- High-speed operation: $t_{pd} = 4.4 \text{ ns (max) (V}_{CC} = 3.0 \text{ to } 3.6 \text{ V)}$

 $t_{pd} = 5.4 \text{ ns (max) (VCC} = 2.3 \text{ to } 2.7 \text{ V)}$

 $t_{pd} = 9.8 \text{ ns (max) (VCC} = 1.8 \text{ V)}$

• Output current: $I_{OH}/I_{OL} = \pm 12 \text{ mA (min) (V}_{CC} = 3.0 \text{ V)}$

 $: I_{OH}/I_{OL} = \pm 8 \text{ mA (min) (V}_{CC} = 2.3 \text{ V)}$

 $: I_{OH}/I_{OL} = \pm 4 \text{ mA (min) (V}_{CC} = 1.8 \text{ V)}$

- Latch-up performance: -300 mA
- ESD performance: Machine model $\geq \pm 200 \text{ V}$

Human body model $\geq \pm 2000 \text{ V}$

- · Package: TSSOP
- Bidirectional interface between 2.5 V and 3.3 V signals.
- 3.6-V tolerant function and power-down protection provided on all inputs and outputs

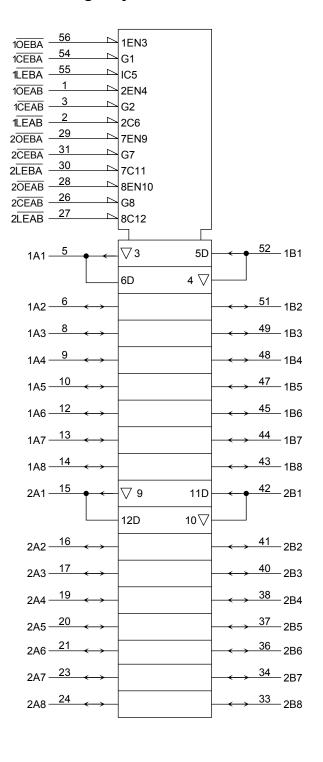
Note: Do not apply a signal to any bus pins when it is in the output mode. Damage may result.

All floating (high impedance) bus pins must have their input level fixed by means of pull-up or pull-down resistors.

Pin Assignment (top view)

10EAB 56 10EBA 1LEAB 1LEBA 55 1CEAB 3 54 1CEBA GND 53 **GND** 5 1B1 1A1 52 1A2 6 51 1B2 V_{CC} 7 50 V_{CC} 1A3 8 1B3 49 9 1A4 48 1B4 1A5 10 47 1B5 GND 11 **GND** 1A6 12 45 1B6 1A7 13 44 1B7 1A8 14 43 1B8 2A1 15 42 2B1 2A2 16 2B2 2A3 17 40 2B3 GND 18 **GND** 39 2A4 19 38 2B4 2A5 20 371 2B5 2A6 21 36 2B6 V_{CC} 22 35 V_{CC} 2A7 23 34 2B7 2A8 24 2B8 33 GND 25 **GND** 32 2CEBA 2CEAB 26 31 2LEAB 27 2LEBA 30 2OEAB 28 29 2OEBA

IEC Logic Symbol



Truth Table (A bus \rightarrow B bus each 8-bit latch)

	Outputs			
CEAB	LEAB	OEAB	Α	В
Н	Х	Х	Х	Z
Х	Х	Н	X	Z
	Н		Х	В0
L	11	L	^	(Note)
L	L	L	L	L
L	L	L	Н	Н

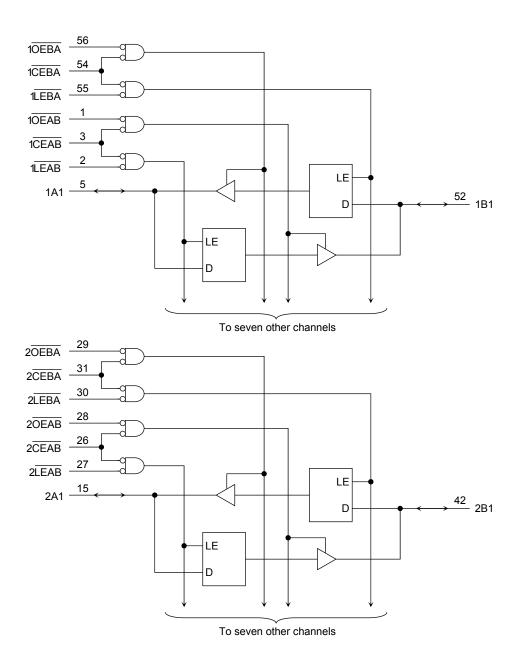
Note: Output level before the indicated steady-state input conditions were established.

Truth Table (B bus → A bus each 8-bit latch)

	Outputs			
CEBA	LEBA	OEBA	В	Α
Н	Х	Х	Х	Z
Х	Х	Н	X	Z
	Н		X	A0
_	"	_	Α	(Note)
L	L	L	L	L
L	L	L	Н	Н

Note: Output level before the indicated steady-state input conditions were established.

System Diagram



4

Absolute Maximum Ratings (Note 1)

Characteristics	Symbol	Rating	Unit
Power supply voltage	V_{CC}	-0.5 to 4.6	V
DC input voltage (OEAB , OEBA , LEAB , LEBA , CEAB , CEBA)	V _{IN}	-0.5 to 4.6	V
		-0.5 to 4.6 (Note 2)	
DC bus I/O voltage	$V_{I/O}$	–0.5 to V _{CC} + 0.5	V
		(Note 3)	
Input diode current	I _{IK}	-50	mA
Output diode current	lok	±50 (Note 4)	mA
DC output current	lout	±50	mA
Power dissipation	P_{D}	400	mW
DC V _{CC} /ground current per supply pin	I _{CC} /I _{GND}	±100	mA
Storage temperature	T _{stg}	−65 to 150	°C

Note 1: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 2: OFF state

Note 3: High or low state. IOUT absolute maximum rating must be observed.

Note 4: $V_{OUT} < GND, V_{OUT} > V_{CC}$

Operating Ranges (Note 1)

Characteristics	Symbol	Rating	Unit	
Power supply voltage	V _{CC}	1.8 to 3.6	V	
Tower supply voltage	v CC	1.2 to 3.6 (Note 2)	V	
Input voltage (OEAB , OEBA , LEAB , LEBA , CEAB , CEBA)	VIN	-0.3 to 3.6	V	
Bus I/O voltage	V _{I/O}	0 to 3.6 (Note 3)	V	
Bus 170 Voltage	V 1/O	0 to V _{CC} (Note 4)		
		±12 (Note 5)		
Output current	I _{OH} /I _{OL}	±8 (Note 6)	mA	
		±4 (Note 7)		
Operating temperature	T _{opr}	-40 to 85	°C	
Input rise and fall time	dt/dv	0 to 10 (Note 8)	ns/V	

Note 1: The operating ranges must be maintained to ensure the normal operation of the device.

Unused inputs must be tied to either VCC or GND.

5

Note 2: Data retention only

Note 3: OFF state

Note 4: High or low state

Note 5: $V_{CC} = 3.0 \text{ to } 3.6 \text{ V}$

Note 6: $V_{CC} = 2.3 \text{ to } 2.7 \text{ V}$

Note 7: $V_{CC} = 1.8 \text{ V}$

Note 8: $V_{IN} = 0.8$ to 2.0 V, $V_{CC} = 3.0$ V



Electrical Characteristics

DC Characteristics (Ta = -40 to 85°C, 2.7 V < $V_{\text{CC}} \leq 3.6 \text{ V})$

Characteri	stics	Symbol	Test Condition		V _{CC} (V)	Min	Max	Unit												
Innut voltage	H-level	V _{IH}	_	_	2.7 to 3.6	2.0	_	V												
Input voltage	L-level	V _{IL}	-	_	2.7 to 3.6	_	0.8	V												
				I _{OH} = -100 μA	2.7 to 3.6	V _{CC} - 0.2														
	H-level	V _{OH}	$V_{IN} = V_{IH}$ or V_{IL}	I _{OH} = -6 mA	2.7	2.2	_													
				$I_{OH} = -8 \text{ mA}$	3.0	2.4														
Output voltage				$I_{OH} = -12 \text{ mA}$	3.0	2.2		V												
		Va	V_{OL} $V_{IN} = V_{IH}$ or V_{IL}	$I_{OL} = 100 \ \mu A$	2.7 to 3.6	_	0.2													
	L-level			$I_{OL} = 6 \text{ mA}$	2.7	_	0.4													
	L-level	VOL		VIN — VIH OI VIL	AIM — AIH OI AIT	AIM — AIM OL AIT	AIM — AIM OI AIT	AIM — AIM OL AIT	VIII VIII OI VIL	AIM — AIM OL AIT	VIN - VIA OI VIL	VIIV — VIH OI VIL	AIM — AIM OL AIT	AIM — AIM OL AIC	AIM — AIH OL AIT	$I_{OL} = 8 \text{ mA}$	3.0	_	0.5	
				I _{OL} = 12 mA	3.0	_	0.8													
Input leakage curre	nt	I _{IN}	V _{IN} = 0 to 3.6 V		2.7 to 3.6	_	±5.0	μΑ												
2 state output OFF	otata aurrant	loz	$V_{IN} = V_{IH}$ or V_{IL}		0.74-0.0		±10.0	μА												
3-state output OFF	3-state output OFF state current		$V_{OUT} = 0$ to 3.6 V		2.7 to 3.6		±10.0	μА												
Power-off leakage of	urrent	I _{OFF}	V _{IN} , V _{OUT} = 0 to 3.6 V		0	_	10.0	μΑ												
Quiescent supply cu	Ouissant auguly aurrent		V _{IN} = V _{CC} or GND		2.7 to 3.6	_	20.0													
Quiescent supply ct	<u></u>	Icc	$V_{CC} \le (V_{IN}, V_{OUT}) \le 3.6 \text{ V}$		2.7 to 3.6	_	±20.0	μΑ												
Increase in I _{CC} per	input	Δlcc	$V_{IH} = V_{CC} - 0.6 V$		2.7 to 3.6	_	750													

DC Characteristics (Ta = -40 to 85°C, 2.3 V \leq V_{CC} \leq 2.7 V)

Characte	ristics	Symbol	Test Condition		V (V)	Min	Max	Unit					
	H-level	V _{IH}			V _{CC} (V)	1.6							
Input voltage	L-level	VIL		_	2.3 to 2.7	_	0.7	V					
		- 11		I _{OH} = -100 μA	2.3 to 2.7	V _{CC} - 0.2	—						
	H-level	Voh	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -4 mA	2.3	2.0	_						
			111 111 12	114 111 12		III III II	I _{OH} = -6 mA	2.3	1.8	_			
Output voltage				$I_{OH} = -8 \text{ mA}$	2.3	1.7	_	V					
			DL VIN = VIH or VIL	I _{OL} = 100 μA	2.3 to 2.7	_	0.2						
	L-level	V _{OL}		$V_{IN} = V_{IH}$ or V_{IL}	$V_{IN} = V_{IH} \ or \ V_{IL}$	$V_{IN} = V_{IH}$ or V_{IL}	$V_{IN} = V_{IH} \ or \ V_{IL}$	$V_{IN} = V_{IH} \ or \ V_{IL}$	I _{OL} = 6 mA	2.3	_	0.4	
				I _{OL} = 8 mA	2.3		0.6						
Input leakage curre	ent	I _{IN}	V _{IN} = 0 to 3.6 V	•	2.3 to 2.7		±5.0	μА					
2 state output OFF	- ototo ourront	1	V _{IN} = V _{IH} or V _{IL}	$V_{IN} = V_{IH}$ or V_{IL}			±10.0	^					
3-state output OFF state current		loz	$V_{OUT} = 0$ to 3.6 V		2.3 to 2.7		±10.0	μΑ					
Power-off leakage	current	loff	V _{IN} , V _{OUT} = 0 to 3.6 V		0	_	10.0	μА					
Out			V _{IN} = V _{CC} or GND		2.3 to 2.7	_	20.0						
Quiescent supply	Current	Icc	$V_{CC} \le (V_{IN}, V_{OUT}) \le$	3.6 V	2.3 to 2.7	_	±20.0	μΑ					



DC Characteristics (Ta = -40 to 85°C, 1.8 V \leq V_{CC} < 2.3 V)

Characteristics		Symbol	Test C	ondition		Min	Max	Unit
Characteris	SilCS	Symbol	Test C	oridition	V _{CC} (V)	IVIIII	IVIAX	Offic
Input voltage	H-level	V _{IH}	-	_	1.8 to 2.3	0.7 × V _{CC}	_	V
input voltage	L-level	V _{IL}	-	_	1.8 to 2.3	ı	0.2 × V _{CC}	V
	H-level	Voh	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -100 μA	1.8	V _{CC} - 0.2	_	
Output voltage				$I_{OH} = -4 \text{ mA}$	1.8	1.4	_	V
	L-level	V _{OL}	V _{IN} = V _{IH} or V _{II}	$I_{OL} = 100 \mu A$	1.8		0.2	
	L-IEVEI	VOL	VIN - VIH OI VIL	I _{OL} = 4 mA	1.8		0.3	
Input leakage currer	nt	I _{IN}	V _{IN} = 0 to 3.6 V		1.8		±5.0	μΑ
3-state output OFF state current		I _{OZ}	$V_{IN} = V_{IH}$ or V_{IL} $V_{OUT} = 0$ to 3.6 V		1.8	_	±10.0	μА
Power-off leakage c	urrent	I _{OFF}	V _{IN} , V _{OUT} = 0 to 3.6 V		0	_	10.0	μА
Quiescent supply cu	Outros and assembly assembly		V _{IN} = V _{CC} or GND		1.8	_	20.0	μА
Quiescerit supply Co	III GIIL	Icc	$V_{CC} \le (V_{IN}, V_{OUT}) \le 3.6 \text{ V}$		1.8	_	±20.0	μΛ



AC Characteristics (Ta = –40 to 85°C, input: $t_r = t_f$ = 2.0 ns, C_L = 30 pF, R_L = 500 Ω) (Note 1)

Characteristics	Symbol	Symbol Test Condition		Min	Max	Unit
Characteristics	Onaractensucs Symbol rest contuition		V _{CC} (V)	IVIIII	IVIAX	Offic
Propagation delay time			1.8	1.5	9.8	
(An, Bn-Bn, An)	t _{pLH} t _{pHL}	Figure 1, Figure 2	2.5 ± 0.2	8.0	5.4	ns
(All, Bli-Bli, All)	фнг		3.3 ± 0.3	0.6	4.4	
Propagation delay time			1.8	1.5	9.8	
(LEAB, LEBA -Bn, An)	t _{pLH}	Figure 1, Figure 2	2.5 ± 0.2	0.8	6.4	ns
(LLAB, LLBA-BII, AII)	t _{pHL}		3.3 ± 0.3	0.6	4.8	
2 state sutput anable time	4		1.8	1.5	9.8	
3-state output enable time (OEAB , OEBA , CEAB , CEBA)	t _{pZL}	Figure 1, Figure 4	2.5 ± 0.2	8.0	5.9	ns
(OLAB, OLBA, CLAB, CLBA)	t _{pZH}		3.3 ± 0.3	0.6	4.3	
2 state output disable time	4		1.8	1.5	8.8	ns
3-state output disable time (OEAB , OEBA , CEAB , CEBA)	t _{pLZ} t _{pHZ}	Figure 1, Figure 4	2.5 ± 0.2	8.0	4.9	
(OLAB, OLBA, CLAB, CLBA)			3.3 ± 0.3	0.6	4.3	
Minimum pulse width	t _{W (L)}	Figure 1, Figure 2, Figure 3	1.8	4.0		
Minimum pulse width (LEAB, LEBA, CEAB, CEBA)			2.5 ± 0.2	1.5	_	ns
(LLAB, LLBA, CLAB, CLBA)			3.3 ± 0.3	1.5	_	
Minimum octun timo			1.8	2.5		
Minimum setup time (An, Bn- \overline{LE} , \overline{CE})	ts	Figure 1, Figure 2, Figure 3	2.5 ± 0.2	1.5		ns
(AII, BII-LE, GE)			3.3 ± 0.3	1.5		
Minimum hold time			1.8	1.0	_	
(An, Bn- $\overline{\text{LE}}$, $\overline{\text{CE}}$)	t _h	Figure 1, Figure 2, Figure 3	2.5 ± 0.2	1.0	_	ns
			3.3 ± 0.3	1.0	_	
			1.8	_	0.5	ns
Output to output skew	tosLH	(Note 2)	2.5 ± 0.2	_	0.5	
	t _{osHL}		3.3 ± 0.3	_	0.5	

8

Note 1: For $C_L = 50 \ pF$, add approximately 300 ps to the AC maximum specification.

Note 2: Parameter guaranteed by design.

 $(t_{OSLH} = |t_{PLHm} - t_{PLHn}|, t_{OSHL} = |t_{PHLm} - t_{PHLn}|)$



Dynamic Switching Characteristics

(Ta = 25°C, input: $t_r = t_f = 2.0 \text{ ns}, C_L = 30 \text{ pF}, R_L = 500 \Omega$)

Characteristics	Symbol	Test Condition	Ī	V _{CC} (V)	Тур.	Unit
		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (No.	ote)	1.8	0.15	
Quiet output maximum dynamic V _{OI}	V _{OLP}	$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (No.	ote)	2.5	0.25	V
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (No.	ote)	3.3	0.35	
		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (No.	ote)	1.8	-0.15	
Quiet output minimum dynamic V _{OI}	V _{OLV}	$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (No.	ote)	2.5	-0.25	V
, 62		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$ (No.	ote)	3.3	-0.35	
		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$ (No.	ote)	1.8	1.55	
Quiet output minimum dynamic V _{OH}	V _{OHV}	$V_{IH} = 2.5 \text{ V}, V_{IL} = 0 \text{ V}$ (No.	ote)	2.5	2.05	V
		V _{IH} = 3.3 V, V _{IL} = 0 V (No	ote)	3.3	2.65	

Note: Parameter guaranteed by design.

Capacitive Characteristics (Ta = 25°C)

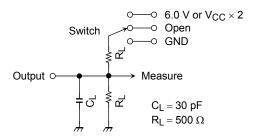
Characteristics	Symbol	Test Condition		Тур.	Unit
Characteristics	Symbol Test Condition		V _{CC} (V)	ιyp.	Offic
Input capacitance	C _{IN}	(OEAB, OEBA, LEAB, LEBA, CEAB, CEBA)	1.8, 2.5, 3.3	6	pF
Bus I/O capacitance	C _{I/O}	_	1.8, 2.5, 3.3	7	pF
Power dissipation capacitance	C _{PD}	$f_{\text{IN}} = 10 \text{ MHz}$ (Note)	1.8, 2.5, 3.3	20	pF

Note: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/16 \text{ (per bit)}$

AC Test Circuit



Parameter	Switch		
t _{pLH} , t _{pHL}	Open		
t _{pLZ} , t _{pZL}	$ \begin{array}{cccccccccccccccccccccccccccccccccccc$		
t _{pHZ} , t _{pZH}	GND		

Figure 1

AC Waveform

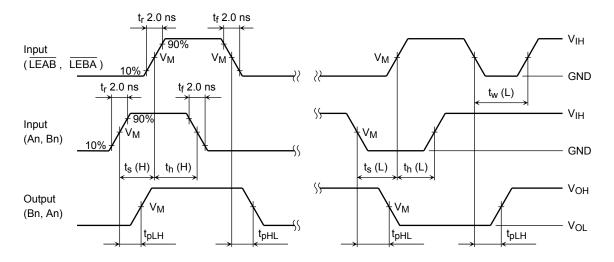


Figure 2 t_{pLH} , t_{pHL} , t_w , t_s , t_h

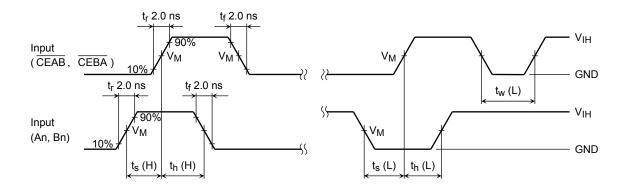


Figure 3 tw, ts, th

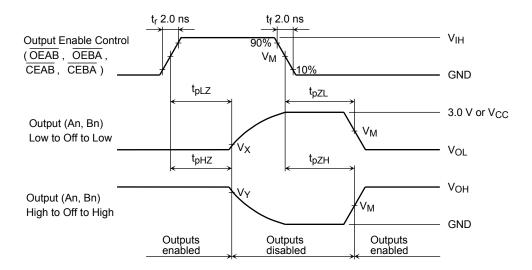


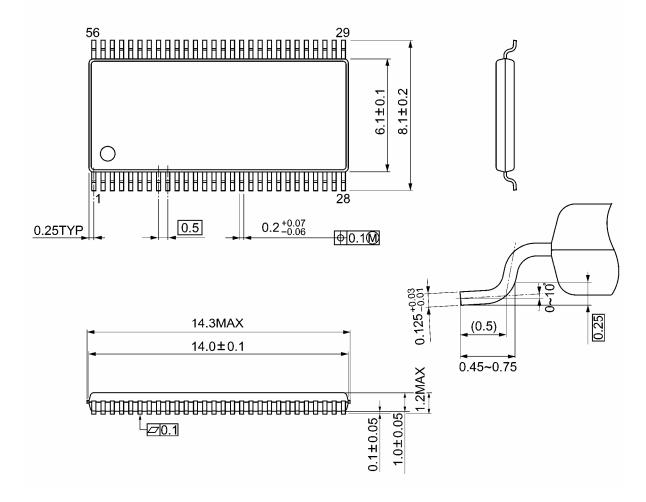
Figure 4 $t_{pLZ}, t_{pHZ}, t_{pZL}, t_{pZH}$

Symbol	V _{CC}							
Syllibol	$3.3\pm0.3~\textrm{V}$	$3.3 \pm 0.3 \text{V}$ $2.5 \pm 0.2 \text{V}$						
V_{IH}	2.7 V	V _{CC}	V _{CC}					
V _M	1.5 V	V _{CC} /2	V _{CC} /2					
VX	V _{OL} + 0.3 V	V _{OL} + 0.15 V	V _{OL} + 0.15 V					
VY	V _{OH} – 0.3 V	V _{OH} – 0.15 V	V _{OH} – 0.15 V					

11

Package Dimensions

TSSOP56-P-0061-0.50A Unit: mm



Weight: 0.25 g (typ.)

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20070701-EN GENERAL

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